



## Description

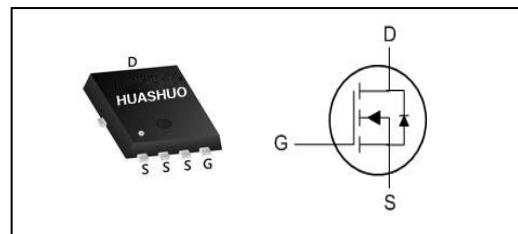
- Advanced Trench Technology
- Low Gate Charge
- 100% UIS Tested
- Low Gate Charge

## Product Summary

$V_{DS}$	40	V
$R_{DS(ON),typ}$	4.7	$m\Omega$
$I_D$	45	A

- SMPS Synchronous Rectification
- DC/DC Converters
- Or-ing

## PRPAK3X3 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_c=25^\circ C$	Continuous Drain Current <sup>1</sup>	45	A
$I_D@T_c=100^\circ C$	Continuous Drain Current <sup>1</sup>	31	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	80	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	68	mJ
$I_{AS}$	Avalanche Current	37	A
$P_D@T_c=25^\circ C$	Total Power Dissipation <sup>4</sup>	27	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	60	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	4.5	°C/W



**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	40	---	---	V
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{\text{GS}}=10\text{V}$ , $I_D=15\text{A}$	---	4.7	6.5	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}$ , $I_D=15\text{A}$	---	7.5	10.5	
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D=250\mu\text{A}$	1.2	1.9	2.2	V
$I_{\text{DSS}}$	Drain-Source Leakage Current	$V_{\text{DS}}=32\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^{\circ}\text{C}$	---	---	1	$\text{uA}$
		$V_{\text{DS}}=32\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=55^{\circ}\text{C}$	---	---	5	
$I_{\text{GSS}}$	Gate-Source Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA
$R_g$	Gate Resistance	$V_{\text{DS}}=0\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	1.9	---	$\Omega$
$Q_g$	Total Gate Charge	$V_{\text{DS}}=20\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $I_D=15\text{A}$	---	20	---	$\text{nC}$
$Q_{\text{gs}}$	Gate-Source Charge		---	3.5	---	
$Q_{\text{gd}}$	Gate-Drain Charge		---	4.2	---	
$T_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}}=20\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $R_G=3\Omega$	---	12	---	$\text{ns}$
$T_r$	Rise Time		---	9.6	---	
$T_{\text{d(off)}}$	Turn-Off Delay Time		---	21	---	
$T_f$	Fall Time		---	16	---	
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}}=20\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	950	---	$\text{pF}$
$C_{\text{oss}}$	Output Capacitance		---	493	---	
$C_{\text{rss}}$	Reverse Transfer Capacitance		---	48	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_s$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0\text{V}$ , Force Current	---	---	45	A
$V_{\text{SD}}$	Diode Forward Voltage <sup>2</sup>	$V_{\text{GS}}=0\text{V}$ , $I_s=1\text{A}$ , $T_J=25^{\circ}\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{\text{DD}}=25\text{V}$ ,  $V_{\text{GS}}=10\text{V}$ ,  $L=0.1\text{mH}$ ,  $I_{\text{AS}}=37\text{A}$
- 4.The power dissipation is limited by  $150^{\circ}\text{C}$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{\text{DM}}$  , in real applications , should be limited by total power dissipation.



### Typical Characteristics

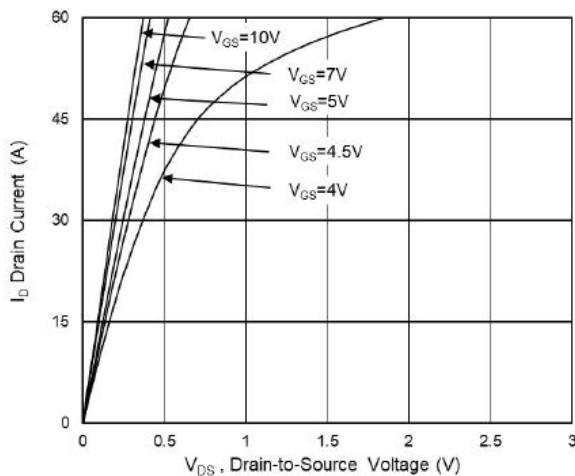


Fig.1 Typical Output Characteristics

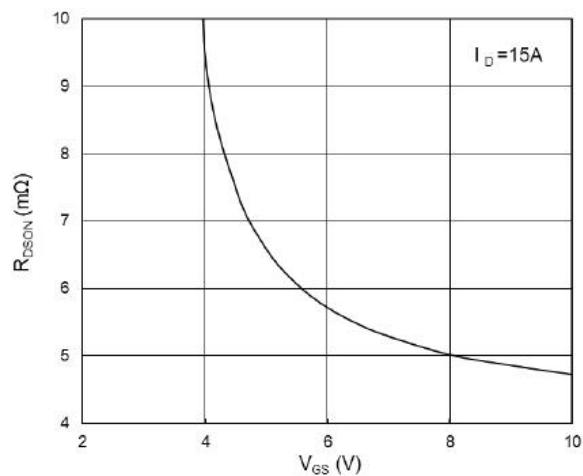


Fig.2 On-Resistance vs. G-S Voltage

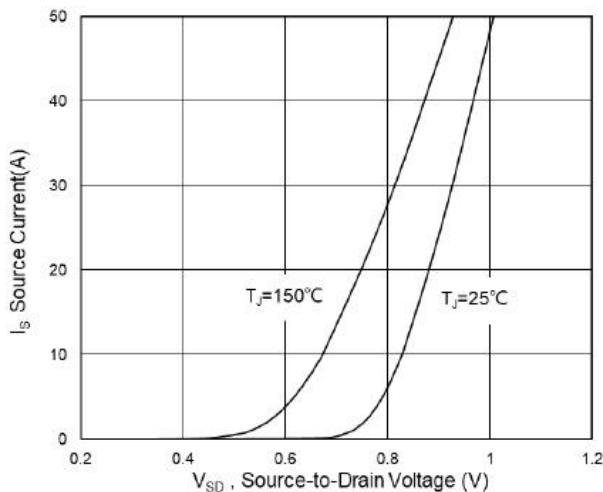


Fig.3 Source Drain Forward Characteristics

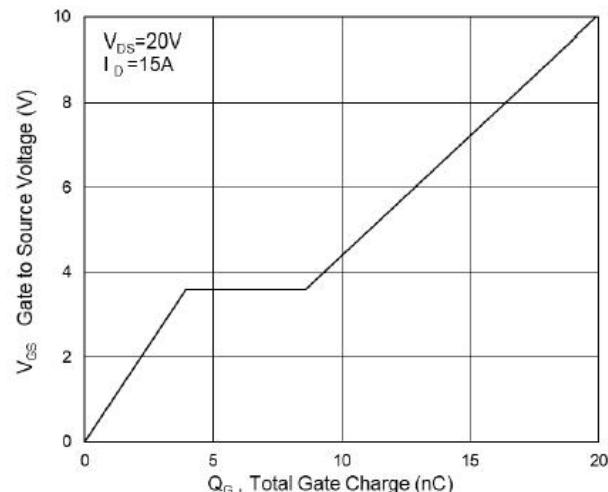


Fig.4 Gate-Charge Characteristics

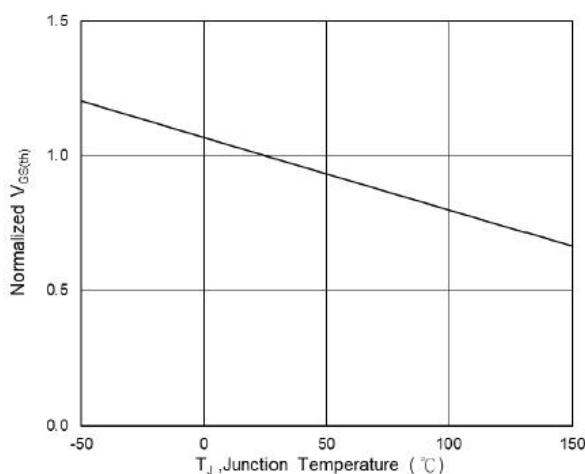


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

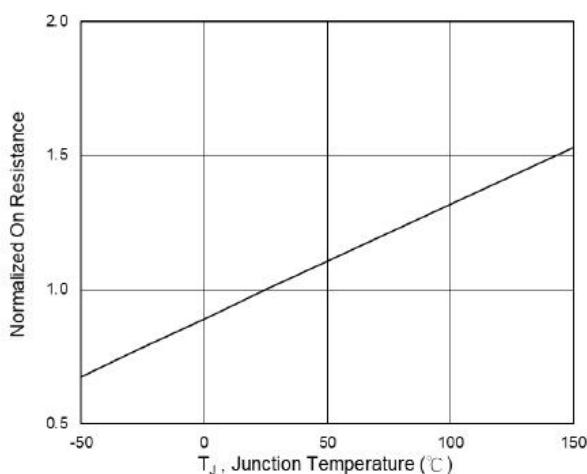


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$



N-Ch 40V Fast Switching MOSFETs

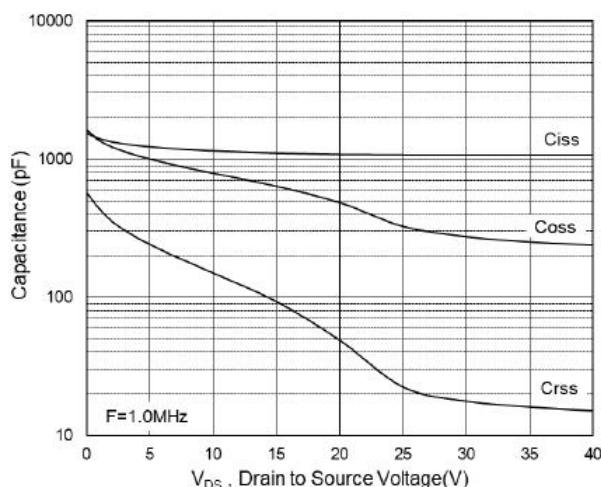


Fig.7 Capacitance

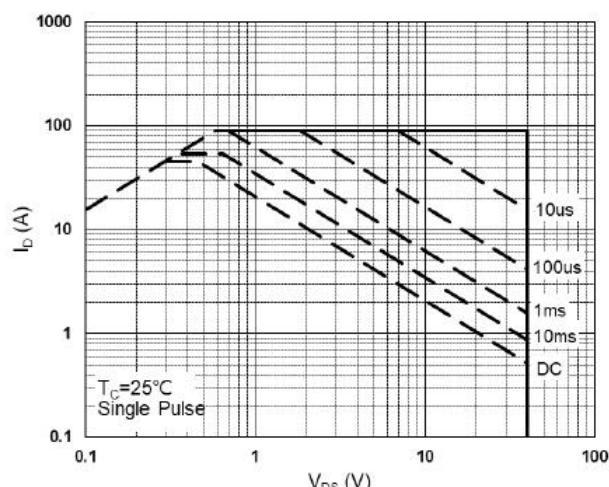


Fig.8 Safe Operating Area

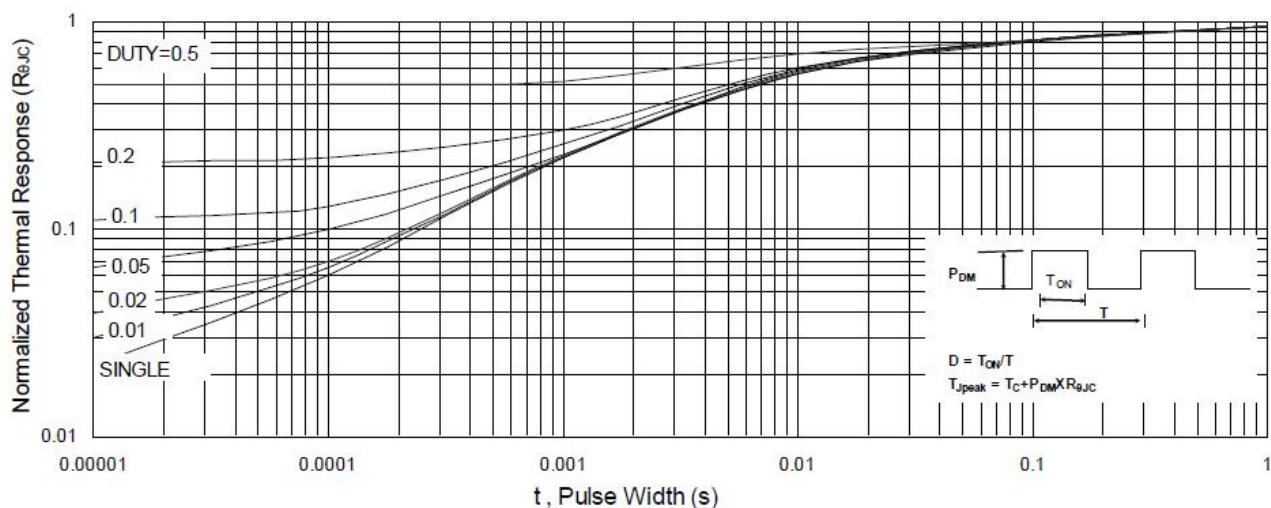


Fig.9 Normalized Maximum Transient Thermal Impedance

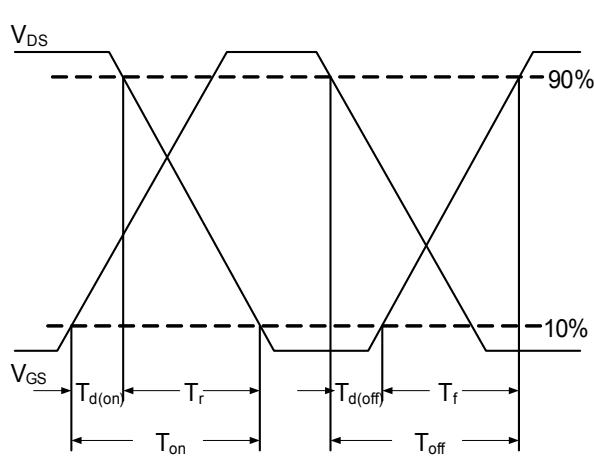


Fig.10 Switching Time Waveform

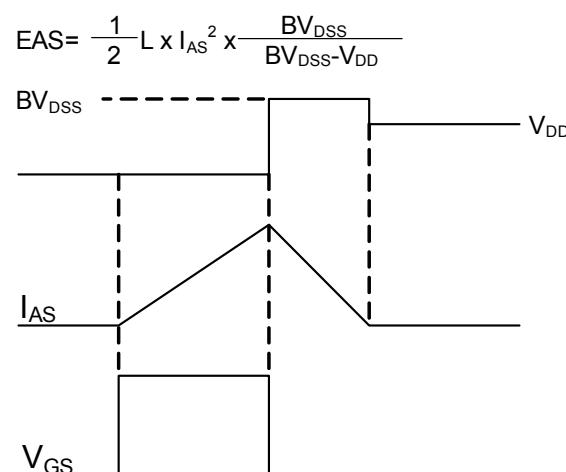


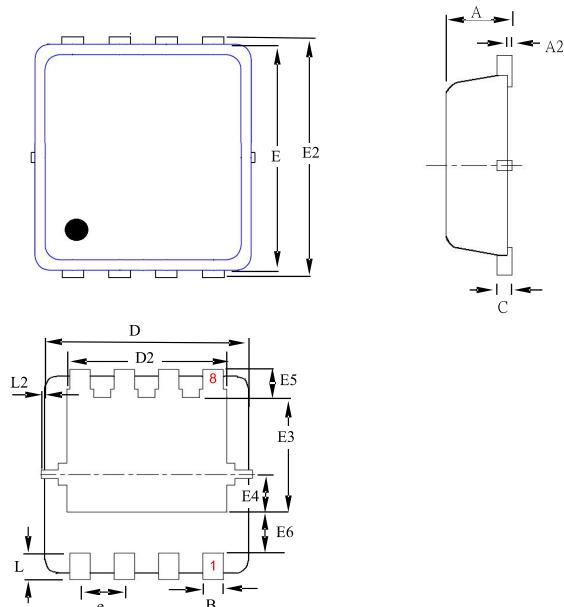
Fig.11 Unclamped Inductive Waveform



## Ordering Information

Part Number	Package code	Packaging
HSBB4054	PRPAK3*3	3000/Tape&Reel

PRPAK 3\*3(E) Single Outline



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.028	0.031	0.035
A2	0.00	--	0.05	0.000	--	0.002
B	0.24	0.30	0.35	0.009	0.012	0.014
C	0.10	0.15	0.25	0.004	0.006	0.010
D	2.90	3.00	3.20	0.114	0.118	0.126
D2	2.15	2.35	2.59	0.085	0.093	0.102
E	2.90	3.00	3.12	0.114	0.118	0.123
E2	3.05	3.20	3.45	0.120	0.126	0.136
E3	1.55	1.75	1.95	0.061	0.069	0.077
E4	0.48	0.58	0.68	0.019	0.023	0.027
E5	0.28	0.43	0.58	0.011	0.017	0.023
E6	0.43	0.63	0.87	0.017	0.025	0.034
L	0.30	0.40	0.50	0.012	0.016	0.020
L2	0.00	--	0.10	0.000	--	0.004
e	--	0.65	--	--	0.026	--